

Product Summary

BV_{DSS}	$R_{DS(ON)} \text{ Max}$	I_D $T_A = +25^\circ\text{C}$
-100V	250m Ω @ $V_{GS} = -10\text{V}$	-2.3A
	300m Ω @ $V_{GS} = -4.5\text{V}$	-2.1A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features and Benefits

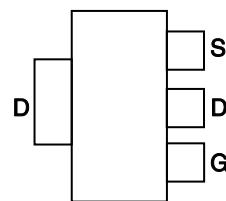
- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

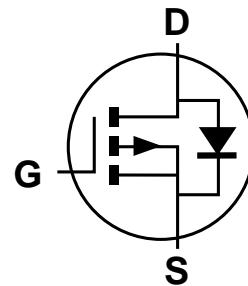
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



Equivalent Circuit

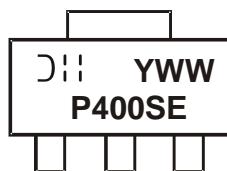
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP10H400SEQ-13	SOT223	2,500 / Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
P400SE = Marking Code
YWW = Date Code Marking
Y or Y = Year (ex: 15 = 2015)
WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = -10\text{V}$ (Note 6)	Steady State	$T_C = +25^\circ\text{C}$ $T_A = +25^\circ\text{C}$	I_D	-6.0 -2.3	A
Maximum Body Diode Forward Current (Note 6)			I_S	-1.9	A
Pulsed Drain Current (380 μs Pulse, Duty Cycle = 1%)			I_{DM}	-10	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	2.0	W
	$T_A = +70^\circ\text{C}$		1.3	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)		P_D	13.7	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.1	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-100	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = -80\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	-1.0	-2.2	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	203	250	$\text{m}\Omega$	$V_{GS} = -10\text{V}, I_D = -5\text{A}$
		—	241	300		$V_{GS} = -4.5\text{V}, I_D = -5\text{A}$
Diode Forward Voltage	V_{SD}	—	-0.9	-1.2	V	$V_{GS} = 0\text{V}, I_S = -5\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1239	—	pF	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	42	—		
Reverse Transfer Capacitance	C_{rss}	—	28	—		
Gate Resistance	R_g	—	13	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	—	8.4	—		
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	—	17.5	—		
Gate-Source Charge	Q_{gs}	—	2.8	—		
Gate-Drain Charge	Q_{gd}	—	3.2	—		
Turn-On Delay Time	$t_{D(\text{ON})}$	—	9.1	—		
Turn-On Rise Time	t_R	—	14.9	—	ns	$V_{DD} = -50\text{V}, R_g = 9.1\Omega, I_D = -5\text{A}$
Turn-Off Delay Time	$t_{D(\text{OFF})}$	—	57.4	—		
Turn-Off Fall Time	t_F	—	34.4	—		
Body Diode Reverse Recovery Time	t_{RR}	—	25.2	—	ns	$V_{GS} = 0\text{V}, I_S = -5\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	24.5	—		

Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

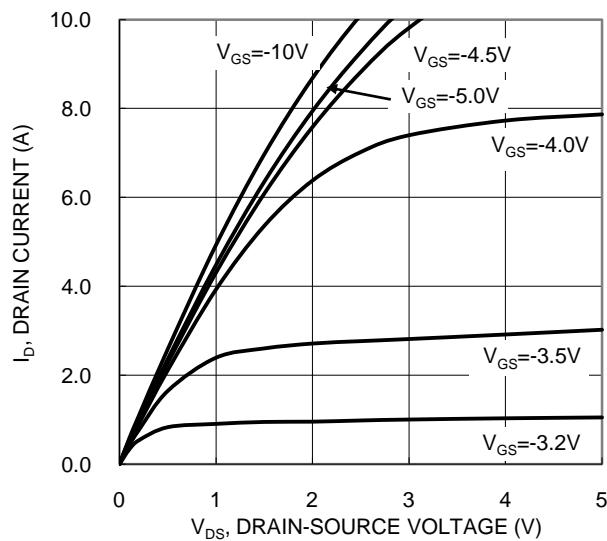


Figure 1. Typical Output Characteristic

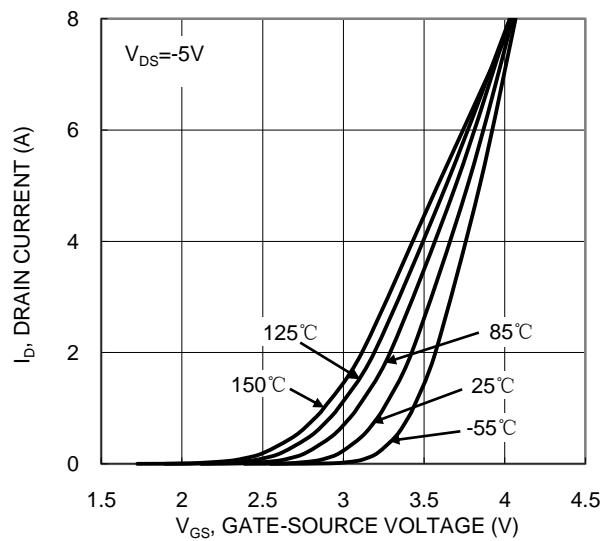


Figure 2. Typical Transfer Characteristic

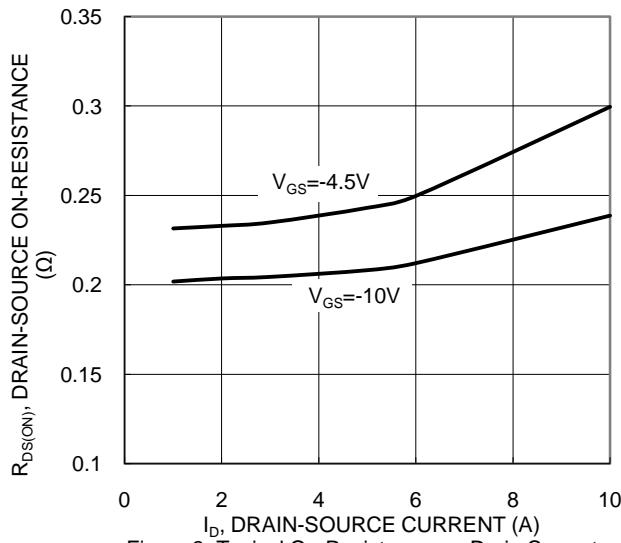


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

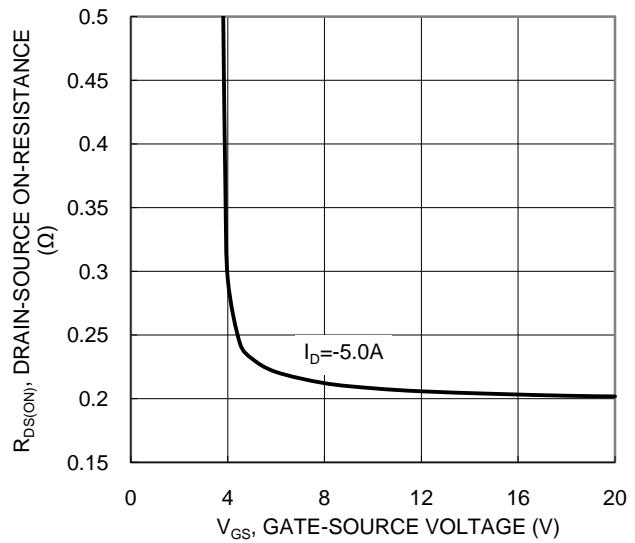


Figure 4. Typical Transfer Characteristic

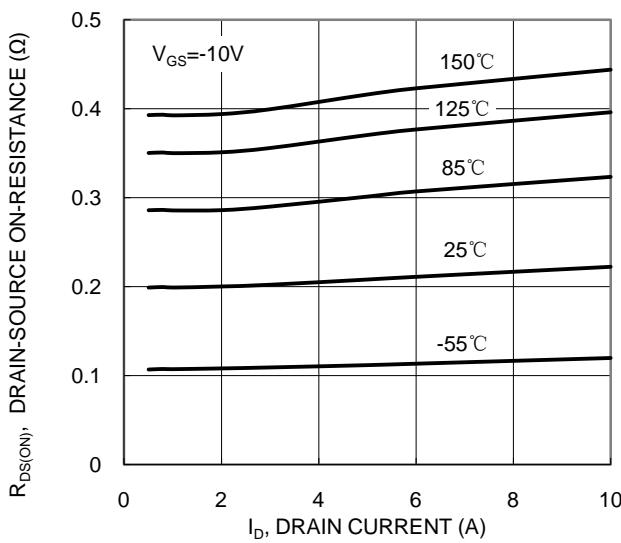


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

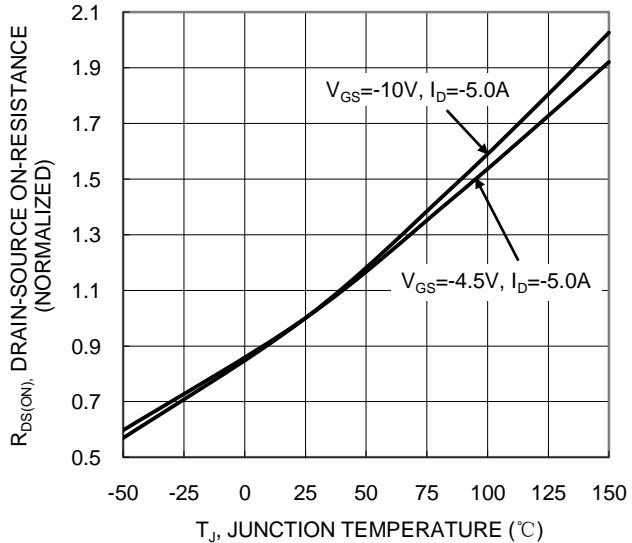


Figure 6. On-Resistance Variation with Junction Temperature

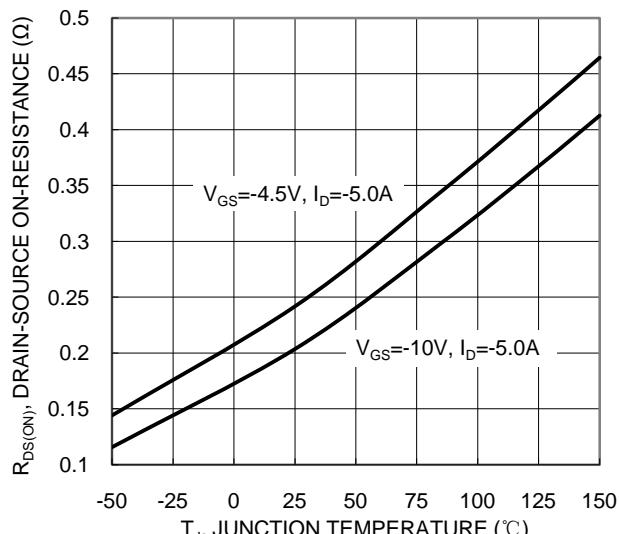


Figure 7. On-Resistance Variation with Junction Temperature

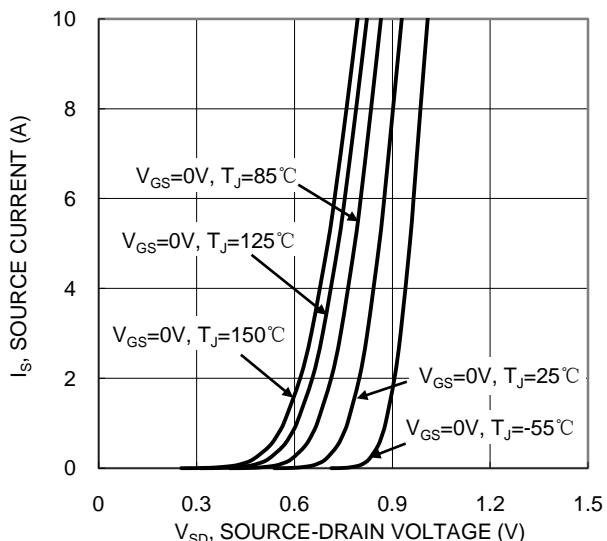


Figure 9. Diode Forward Voltage vs. Current

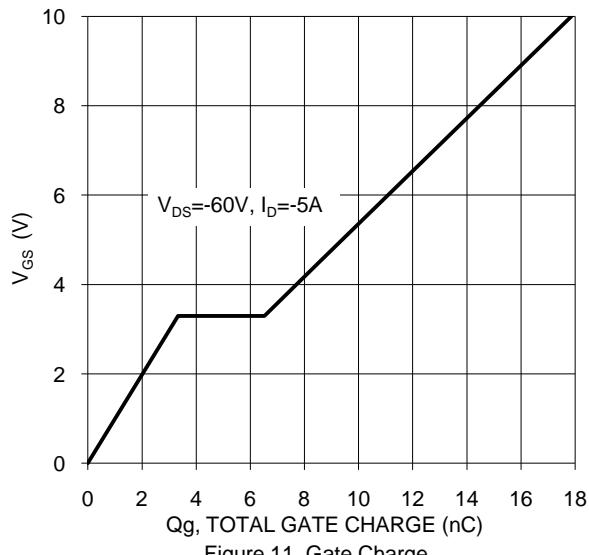


Figure 11. Gate Charge

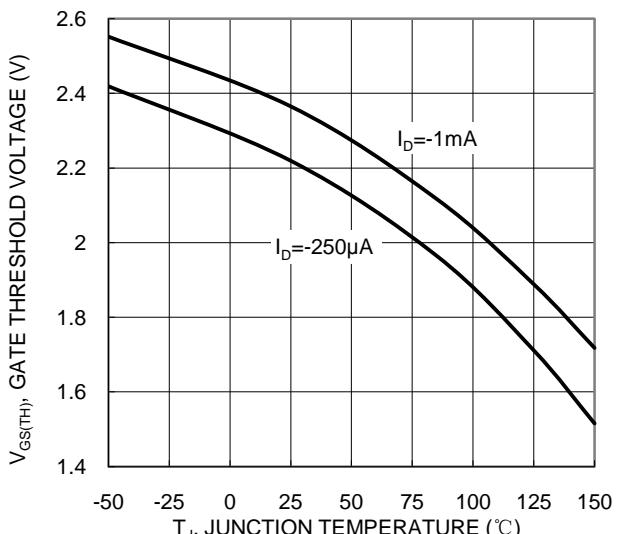


Figure 8. Gate Threshold Variation vs. Junction Temperature

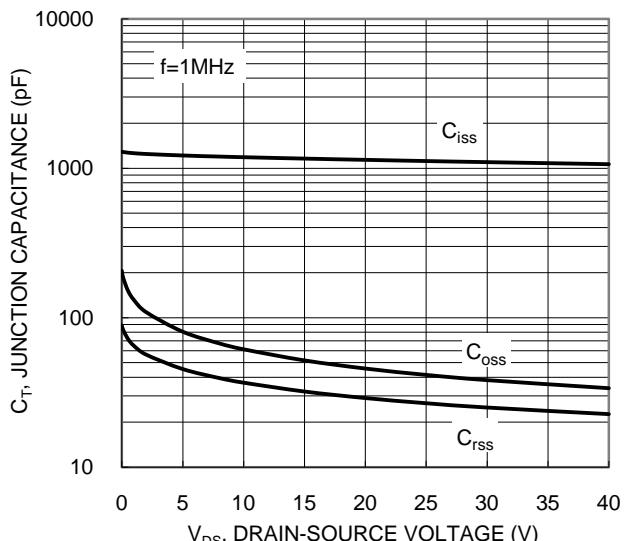


Figure 10. Typical Junction Capacitance

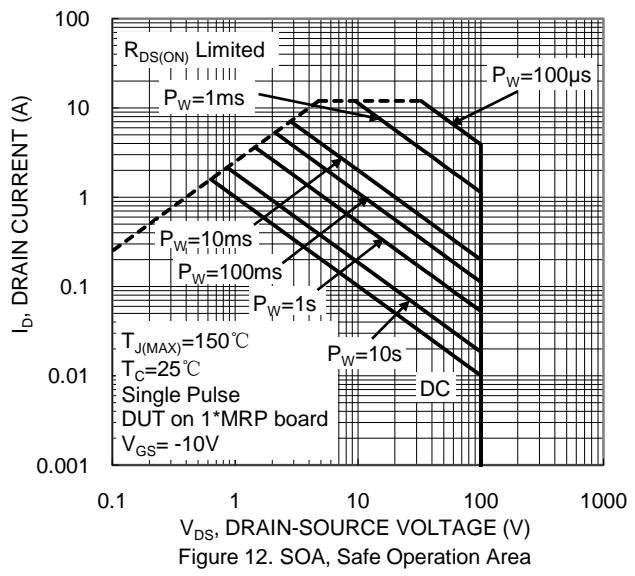
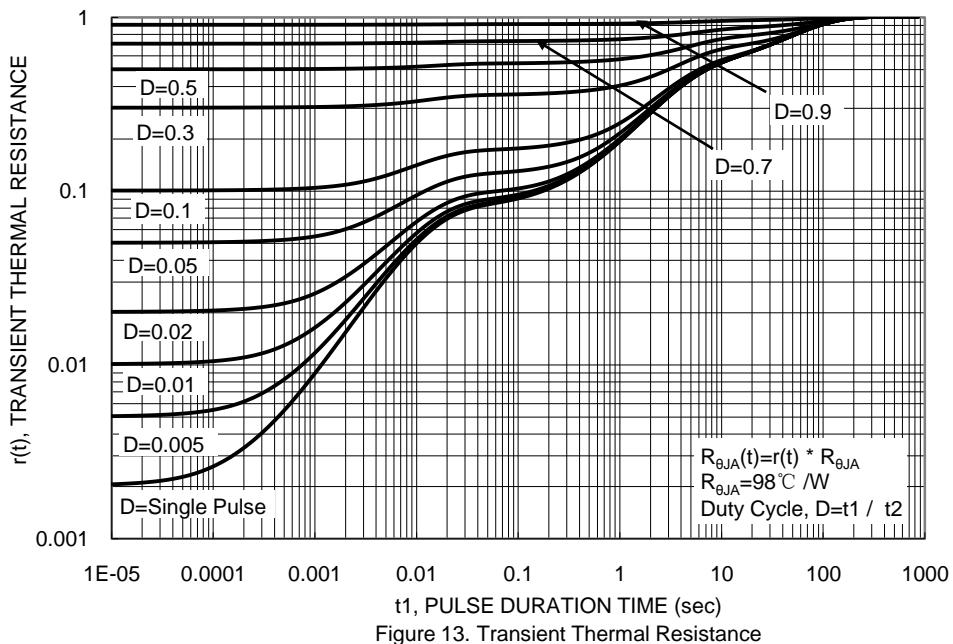


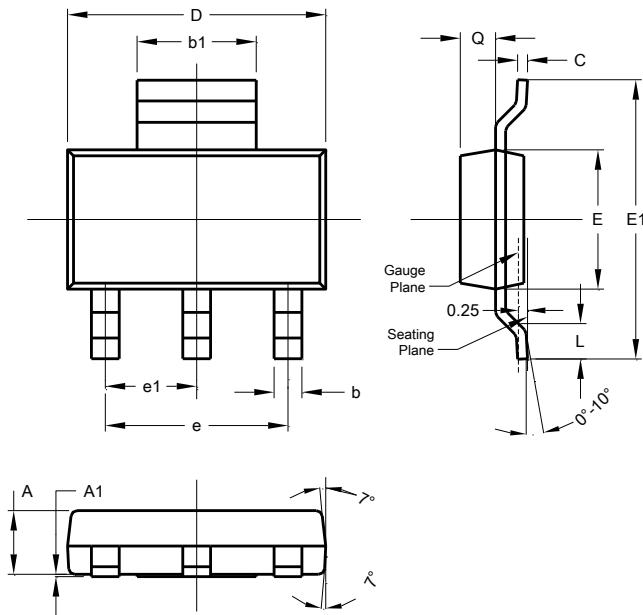
Figure 12. SOA, Safe Operation Area



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SOT223



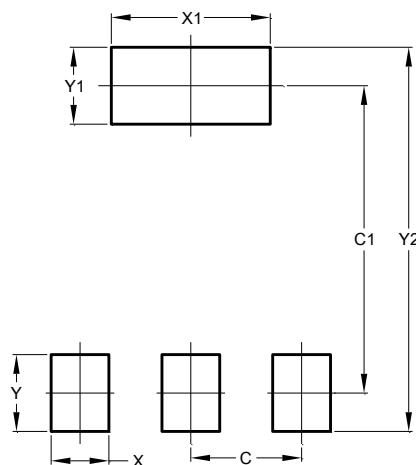
SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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